

ANEXO I



September 1983
Revised January 2005

MM74HC00 Quad 2-Input NAND Gate

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General Description

The MM74HC00 NAND gates utilize advanced silicon-gate CMOS technology to achieve operating speeds similar to LS-TTL gates with the low power consumption of standard CMOS integrated circuits. All gates have buffered outputs. All devices have high noise immunity and the ability to drive 10 LS-TTL loads. The 74HC logic family is functionally as well as pin-out compatible with the standard 74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

Features

- Typical propagation delay: 8 ns
- Wide power supply range: 2–6V
- Low quiescent current: 20 μ A maximum (74HC Series)
- Low input current: 1 μ A maximum
- Fanout of 10 LS-TTL loads

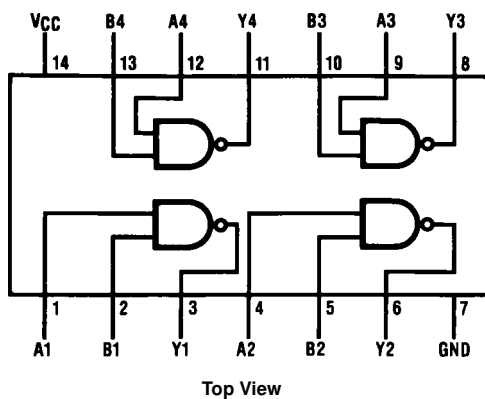
Ordering Code:

Order Number	Package Number	Package Description
MM74HC00M	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
MM74HC00MX_NL	M14A	Pb-Free 14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
MM74HC00SJ	M14D	Pb-Free 14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
MM74HC00MTC	MTC14	14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
MM74HC00MTCX_NL	MTC14	Pb-Free 14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
MM74HC00N	N14A	14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide
MM74HC00N_NL	N14A	Pb-Free 14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide

Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.
Pb-Free package per JEDEC J-STD-020B.

Connection Diagram

Pin Assignments for DIP, SOIC, SOP and TSSOP



Absolute Maximum Ratings(Note 1)

(Note 2)

Supply Voltage (V_{CC})	−0.5 to +7.0V
DC Input Voltage (V_{IN})	−1.5 to $V_{CC}+1.5V$
DC Output Voltage (V_{OUT})	−0.5 to $V_{CC}+0.5V$
Clamp Diode Current (I_{IK} , I_{OK})	±20 mA
DC Output Current, per pin (I_{OUT})	±25 mA
DC V_{CC} or GND Current, per pin (I_{CC})	±50 mA
Storage Temperature Range (T_{STG})	−65°C to +150°C
Power Dissipation (P_D)	
(Note 3)	600 mW
S.O. Package only	500 mW
Lead Temperature (T_L)	
(Soldering 10 seconds)	260°C

Recommended Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage	0	V_{CC}	V
(V_{IN} , V_{OUT})			
Operating Temperature Range (T_A)	−40	+85	°C
Input Rise or Fall Times			
(t_r , t_f) $V_{CC} = 2V$		1000	ns
$V_{CC} = 4.5V$		500	ns
$V_{CC} = 6.0V$		400	ns

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.**Note 2:** Unless otherwise specified all voltages are referenced to ground.**Note 3:** Power Dissipation temperature derating — plastic “N” package: −12 mW/°C from 65°C to 85°C.**DC Electrical Characteristics** (Note 4)

Symbol	Parameter	Conditions	V _{CC}	T _A = 25°C		T _A = −40 to 85°C	T _A = −55 to 125°C	Units
				Typ	Guaranteed Limits			
V _{IH}	Minimum HIGH Level Input Voltage		2.0V		1.5	1.5	1.5	V
			4.5V		3.15	3.15	3.15	V
			6.0V		4.2	4.2	4.2	V
V _{IL}	Maximum LOW Level Input Voltage		2.0V		0.5	0.5	0.5	V
			4.5V		1.35	1.35	1.35	V
			6.0V		1.8	1.8	1.8	V
V _{OH}	Minimum HIGH Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 20 μA	2.0V	2.0	1.9	1.9	1.9	V
			4.5V	4.5	4.4	4.4	4.4	V
			6.0V	6.0	5.9	5.9	5.9	V
		V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 4.0 mA I _{OUT} ≤ 5.2 mA	4.5V	4.2	3.98	3.84	3.7	V
			6.0V	5.7	5.48	5.34	5.2	V
V _{OL}	Maximum LOW Level Output Voltage	V _{IN} = V _{IH} I _{OUT} ≤ 20 μA	2.0V	0	0.1	0.1	0.1	V
			4.5V	0	0.1	0.1	0.1	V
			6.0V	0	0.1	0.1	0.1	V
		V _{IN} = V _{IH} I _{OUT} ≤ 4.0 mA I _{OUT} ≤ 5.2 mA	4.5V	0.2	0.26	0.33	0.4	V
			6.0V	0.2	0.26	0.33	0.4	V
I _{IN}	Maximum Input Current	V _{IN} = V _{CC} or GND	6.0V		±0.1	±1.0	±1.0	μA
I _{CC}	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND I _{OUT} = 0 μA	6.0V		2.0	20	40	μA

Note 4: For a power supply of 5V ±10% the worst case output voltages (V_{OH} and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at $V_{CC} = 5.5V$ and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN} , I_{CC} , and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

AC Electrical Characteristics
 $V_{CC} = 5V$, $T_A = 25^\circ C$, $C_L = 15\text{ pF}$, $t_r = t_f = 6\text{ ns}$

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL} , t_{PLH}	Maximum Propagation Delay		8	15	ns

AC Electrical Characteristics
 $V_{CC} = 2.0V$ to $6.0V$, $C_L = 50\text{ pF}$, $t_r = t_f = 6\text{ ns}$ (unless otherwise specified)

Symbol	Parameter	Conditions	V _{CC}	T _A = 25°C		T _A = −40 to 85°C	T _A = −55 to 125°C	Units
				Typ	Guaranteed Limits			
t _{PHL} , t _{PLH}	Maximum Propagation Delay		2.0V	45	90	113	134	ns
			4.5V	9	18	23	27	ns
			6.0V	8	15	19	23	ns
t _{TLH} , t _{THL}	Maximum Output Rise and Fall Time		2.0V	30	75	95	110	ns
			4.5V	8	15	19	22	ns
			6.0V	7	13	16	19	ns
C _{PD}	Power Dissipation Capacitance (Note 5)	(per gate)		20				pF
C _{IN}	Maximum Input Capacitance			5	10	10	10	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.



M74HC05

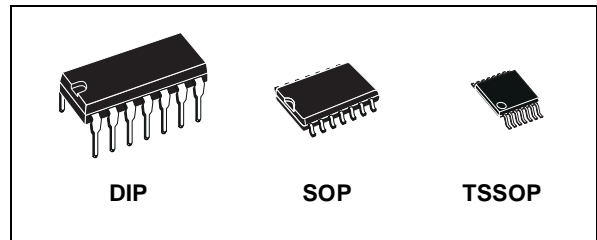
HEX INVERTER (OPEN DRAIN)

- **HIGH SPEED:**
 $t_{PD} = 10\text{ns}$ (TYP.) at $V_{CC} = 6\text{V}$
- **LOW POWER DISSIPATION:**
 $I_{CC} = 1\mu\text{A}$ (MAX.) at $T_A = 25^\circ\text{C}$
- **HIGH NOISE IMMUNITY:**
 $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (MIN.)
- **WIDE OPERATING VOLTAGE RANGE:**
 $V_{CC} \text{ (OPR)} = 2\text{V to } 6\text{V}$
- **PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 05**

DESCRIPTION

The M74HC05 is an high speed CMOS HEX INVERTER (OPEN DRAIN) fabricated with silicon gate C²MOS technology.

The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output.

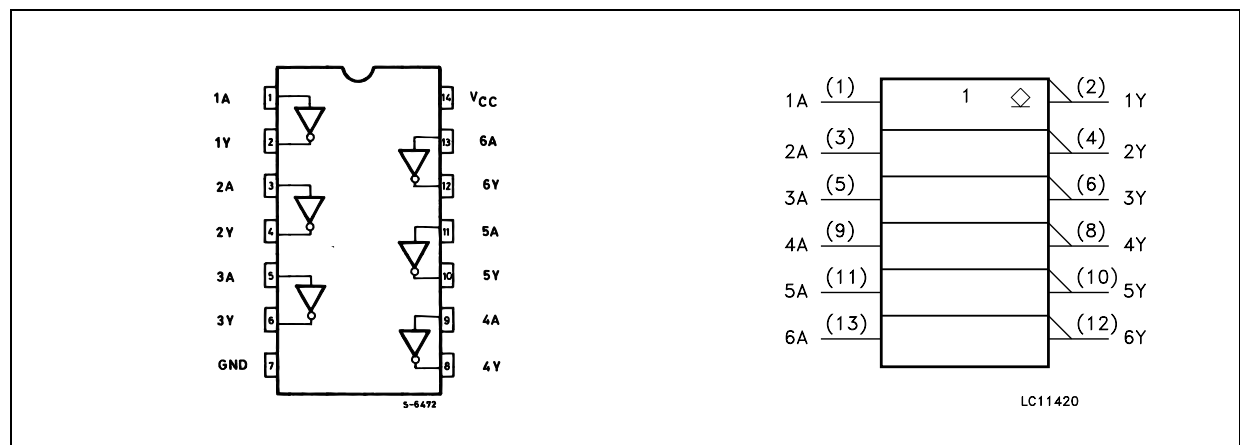


ORDER CODES

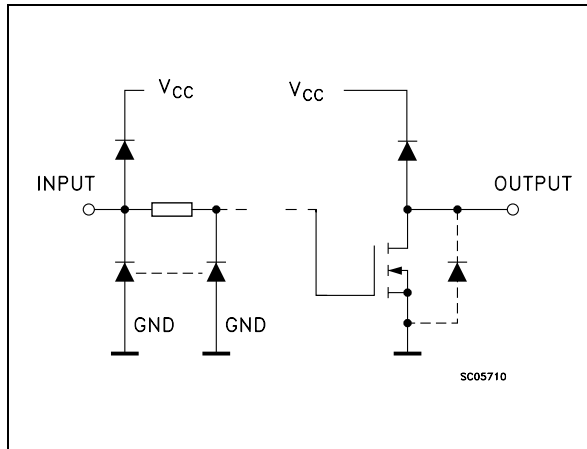
PACKAGE	TUBE	T & R
DIP	M74HC05B1R	
SOP	M74HC05M1R	M74HC05RM13TR
TSSOP		M74HC05TTR

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 3, 5, 9, 11, 13	1A to 6A	Data Inputs
2, 4, 6, 8, 10, 12	1Y to 6Y	Data Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

TRUTH TABLE

A	Y
L	Z
H	L

Z : High Impedance

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P _D	Power Dissipation	500(*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2 to 6	V
V _I	Input Voltage	0 to V _{CC}	V
V _O	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 2.0V	0 to 1000
		V _{CC} = 4.5V	0 to 500
		V _{CC} = 6.0V	0 to 400

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value								Unit
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C			
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.		
V _{IH}	High Level Input Voltage	2.0		1.5			1.5		1.5		V	
		4.5		3.15			3.15		3.15			
		6.0		4.2			4.2		4.2			
V _{IL}	Low Level Input Voltage	2.0				0.5		0.5		0.5	V	
		4.5				1.35		1.35		1.35		
		6.0				1.8		1.8		1.8		
V _{OL}	Low Level Output Voltage	2.0	I _O =20 μA		0.0	0.1		0.1		0.1	V	
		4.5	I _O =20 μA		0.0	0.1		0.1		0.1		
		6.0	I _O =20 μA		0.0	0.1		0.1		0.1		
		4.5	I _O =4.0 mA		0.17	0.26		0.33		0.40		
		6.0	I _O =5.2 mA		0.18	0.26		0.33		0.40		
I _I	Input Leakage Current	6.0	V _I = V _{CC} or GND			± 0.1		± 1		± 1	μA	
I _{OZ}	Output Leakage Current	6.0	V _I = V _{IH} or V _{IL} V _O = V _{CC} or GND			±0.5		± 5		± 10	μA	
I _{CC}	Quiescent Supply Current	6.0	V _I = V _{CC} or GND			1		10		20	μA	

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6ns)

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t _{THL}	Output Transition Time	2.0			30	75		95		110	ns
		4.5			8	15		19		22	
		6.0			7	13		16		19	
t _{PLZ}	Propagation Delay Time	2.0	R _L = 1 KΩ		20	90		115		135	ns
		4.5			11	18		23		27	
		6.0			10	15		20		23	
t _{PZL}	Propagation Delay Time	2.0	R _L = 1 KΩ		33	90		115		135	ns
		4.5			9	18		23		27	
		6.0			8	15		20		23	